

L Number	Hits	Search Text	DB	Time stamp
1	1288	ellipsometry	USPAT	2002/11/15 13:11
2	589379	silicon naer2 oxide	USPAT	2002/11/15 13:12
3	288635	silicon naer2 nitirde	USPAT	2002/11/15 13:12
4	927	((silicon naer2 nitirde) and (silicon naer2 oxide) and ellipsometry	USPAT	2002/11/15 13:12
5	1137	ellipsometry and thickness	USPAT	2002/11/15 13:12
6	1137	((ellipsometry and thickness) and thickness	USPAT	2002/11/15 13:12
7	860	((silicon naer2 nitirde) and (silicon naer2 oxide) and ellipsometry) and thickness	USPAT	2002/11/15 13:13
9	789	((silicon naer2 nitirde) and (silicon naer2 oxide) and ellipsometry) and thickness) and time	USPAT	2002/11/15 13:13
10	672	((silicon naer2 nitirde) and (silicon naer2 oxide) and ellipsometry) and thickness) and time) and (wafer semiconductor)	USPAT	2002/11/15 13:15
11	410	((silicon naer2 nitirde) and (silicon naer2 oxide) and ellipsometry) and thickness) and time) and (wafer semiconductor)) and (etch\$3 engrav\$3)	USPAT	2002/11/15 13:16
12	26	((silicon naer2 nitirde) and (silicon naer2 oxide) and ellipsometry) and thickness) and time) and (wafer semiconductor)) and (etch\$3 engrav\$3)) and (optical near5 emission)	USPAT	2002/11/15 13:18
13	21	((silicon naer2 nitirde) and (silicon naer2 oxide) and ellipsometry) and thickness) and time) and (wafer semiconductor)) and (etch\$3 engrav\$3)) and (optical near5 emission)) and ((measur\$3 determin\$3) near5 thickness)	USPAT	2002/11/15 13:19
-	51948	measur\$3 near20 thickness	USPAT; US-PGPUB	2002/10/30 13:49
-	9538	((measur\$3 near20 thickness) and (etch\$3 engrav\$3)	USPAT; US-PGPUB	2002/10/30 13:50
-	6466	((measur\$3 near20 thickness) and (etch\$3 engrav\$3)) and (dielectric insulat\$3 (silicon near3 nitride) (silicon near3 oxide) ("Si.sub.3" adj2 "N.sub.4") ("Si" adj2 "O.sub.2"))	USPAT; US-PGPUB	2002/10/30 13:53
-	4021	((measur\$3 near20 thickness) and (etch\$3 engrav\$3)) and (dielectric insulat\$3 (silicon near3 nitride) (silicon near3 oxide) ("Si.sub.3" adj2 "N.sub.4") ("Si" adj2 "O.sub.2"))) and (optical emission spectrum distribution)	USPAT; US-PGPUB	2002/10/30 13:55
-	622	((measur\$3 near20 thickness) and (etch\$3 engrav\$3)) and (dielectric insulat\$3 (silicon near3 nitride) (silicon near3 oxide) ("Si.sub.3" adj2 "N.sub.4") ("Si" adj2 "O.sub.2"))) and (optical emission spectrum distribution)) and amplitude	USPAT; US-PGPUB	2002/10/30 13:56
-	587	((measur\$3 near20 thickness) and (etch\$3 engrav\$3)) and (dielectric insulat\$3 (silicon near3 nitride) (silicon near3 oxide) ("Si.sub.3" adj2 "N.sub.4") ("Si" adj2 "O.sub.2"))) and (optical emission spectrum distribution)) and amplitude) and time	USPAT; US-PGPUB	2002/10/30 13:56
-	566	((measur\$3 near20 thickness) and (etch\$3 engrav\$3)) and (dielectric insulat\$3 (silicon near3 nitride) (silicon near3 oxide) ("Si.sub.3" adj2 "N.sub.4") ("Si" adj2 "O.sub.2"))) and (optical emission spectrum distribution)) and amplitude) and time) and (semiconductor wafer substrate)	USPAT; US-PGPUB	2002/10/30 13:57

-	475	(((((measur\$3 near20 thickness) and (etch\$3 engrav\$3)) and (dielectric insulat\$3 (silicon near3 nitride) (silicon near3 oxide) ("Si.sub.3" adj2 "N.sub.4") ("Si" adj2 "O.sub.2")))) and (optical emission spectrum distribution)) and amplitude) and time) and (semiconductor wafer substrate)	USPAT	2002/10/31 10:35
-	91	(((((measur\$3 near20 thickness) and (etch\$3 engrav\$3)) and (dielectric insulat\$3 (silicon near3 nitride) (silicon near3 oxide) ("Si.sub.3" adj2 "N.sub.4") ("Si" adj2 "O.sub.2")))) and (optical emission spectrum distribution)) and amplitude) and time) and (semiconductor wafer substrate)	US-PGPUB; EPO	2002/10/31 10:13
-	92	(((((measur\$3 near20 thickness) and (etch\$3 engrav\$3)) and (dielectric insulat\$3 (silicon near3 nitride) (silicon near3 oxide) ("Si.sub.3" adj2 "N.sub.4") ("Si" adj2 "O.sub.2")))) and (optical emission spectrum distribution)) and amplitude) and time) and (semiconductor wafer substrate)	US-PGPUB; EPO	2002/10/31 10:13
-	1157	(((((measur\$3 determin\$5) near20 thickness) and (etch\$3 polish\$3 engrav\$3)) and (dielectric insulat\$3 (silicon near3 nitride) (silicon near3 oxide) ("Si.sub.3" adj2 "N.sub.4") ("Si" adj2 "O.sub.2")))) and (optical emission spectrum distribution)) and amplitude) and time) and (semiconductor wafer substrate)	USPAT	2002/10/31 11:16
-	42035	e2prom eeprom eprom) (flash near5 memory	USPAT	2002/10/31 10:55
-	39	(e2prom eeprom eprom) (flash near5 memory) and ((((((measur\$3 determin\$5) near20 thickness) and (etch\$3 polish\$3 engrav\$3)) and (dielectric insulat\$3 (silicon near3 nitride) (silicon near3 oxide) ("Si.sub.3" adj2 "N.sub.4") ("Si" adj2 "O.sub.2")))) and (optical emission spectrum distribution)) and amplitude) and time)	USPAT	2002/10/31 10:57
-	1	(((((measur\$3 determin\$5) near20 thickness) and (etch\$3 polish\$3 engrav\$3)) and (dielectric insulat\$3 (silicon near3 nitride) (silicon near3 oxide) ("Si.sub.3" adj2 "N.sub.4") ("Si" adj2 "O.sub.2")))) and (optical emission spectrum distribution)) and amplitude) and time) and (semiconductor wafer substrate)	EPO; JPO; DERWENT; IBM_TDB	2002/10/31 11:29
-	3	thickness same measur\$3 same time same etch\$3 same emission same spectrum	USPAT	2002/10/31 11:32
-	1973	thickness and measur\$3 and time and etch\$3 and emission and spectrum	USPAT	2002/10/31 11:33
-	204	(thickness and measur\$3 and time and etch\$3 and emission and spectrum) and (ONO (oxide near5 nitride near5 oxide))	USPAT	2002/10/31 11:34